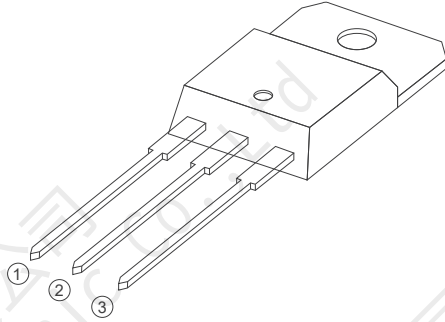


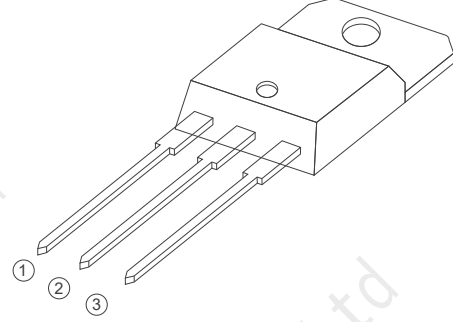
TYN620 Series
20A SCRs
Standard SCRs



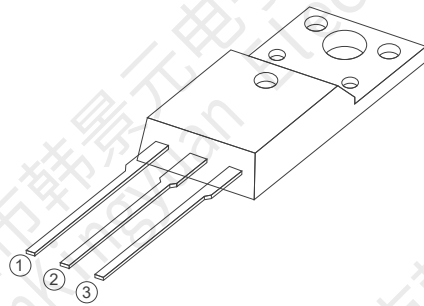
ShenZhenHanKingyuan
Electronic CO.,Ltd



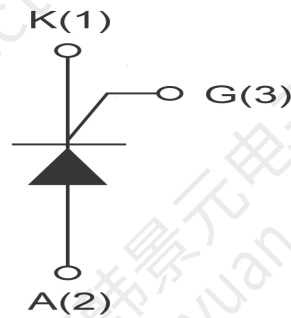
TO-220A Insulated



TO-220B Non-Insulated



TO-220F Insulated



FEATURES

> IT(RMS):20A > VGT: 1.5V > VDRM VRRM:600Vand800V

APPLICATIONS

Washing machine,vacuums, massager,solid state relay, AC Motor speed regulation and so on.

Absolute Maximum Ratings (T_j=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
VDRM VRRM	Repetitive Peak Off-State Voltage	TYN620/TYN820	600/800	V
IT(RMS)	R.M.S On-State Current		20	A
IT(AV)	average On-State Current		13	A
ITSM	Surge On-State Current	F=50Hz, tp=10ms	200	A
I ² t	I ² t for fusing	Tp=10ms	200	A ² s
PG(AV)	Average Gate Power Dissipation	Tj=125°C	1	W
PGM	Peak Gate Current	Tj=125°C	5	W
Tj	Operating Junction Temperature		~40~125	°C
TSTG	Storage Temperature		~40~150	°C

Electrical Characteristics (T_j=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Value	Unit
IDRM	Repetitive Peak Off-State Current	Tc=25°C	≤10	uA
		Tc=125°C	≤1	mA
IRRM	Repetitive Peak Reverse Current	Tc=25°C	≤10	uA
		Tc=125°C	≤1	mA
VTM	Forward "on" voltage	IT=30A tp=380us	≤1.6	V
VGD	Gate nontrigger voltage	VD=VDRM, Tj=125°C, RL=3.3KΩ	≥0.25	V
IL	Latching current	IG=1.2IGT	≤60	mA
IH	Holding current	VD=12V, IGT=0.1A	≤40	mA
VGT	Gate trigger voltage	VD=12V	≤1.0	V
IGT	Gate trigger current	VD=12V, IT=0.1A	≤25	mA
dv/dt	Critical-rate of rise of commutation voltage	VD=2/3VDRM, Tj=110°C, RGK=1KΩ	≥500	V/us
di/dt	Critical-rate of rise of commutation current	IG=2XIG, tr≤100us, Tj=125°C	≥50	A/us
Rth(j-c)	Thermal resistance	Junction to case	1.0	°C/W
Rth(j-a)	Thermal resistance	Junction to ambient	50	°C/W

FIG1

Maximum power dissipation versus RMS on-state current

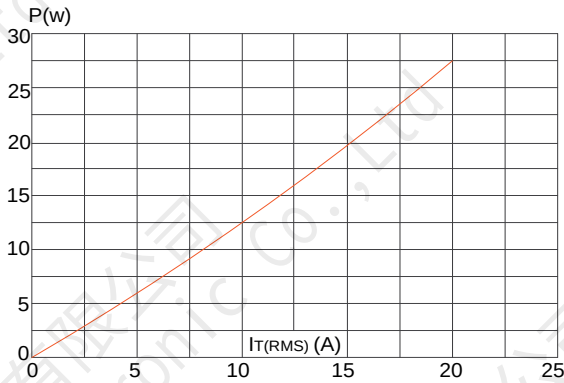


FIG2

RMS on-state current versus case temperature

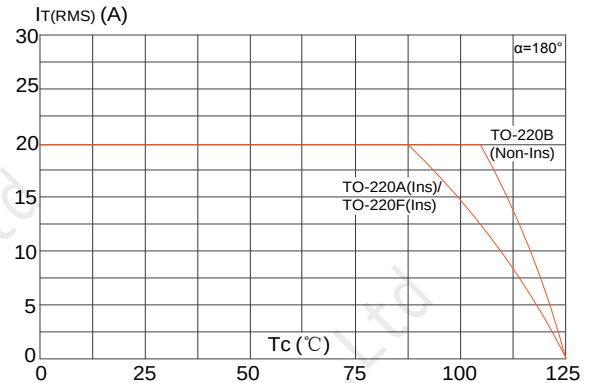


FIG3

Surge peak on-state current versus number of cycles

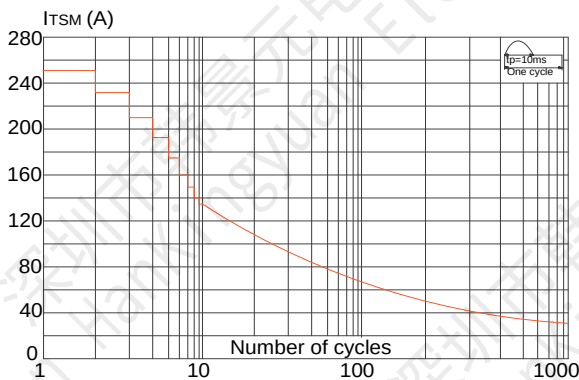


FIG4

On-state characteristics (maximum values)

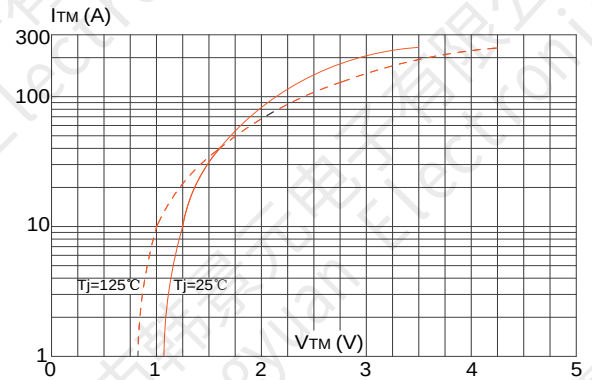


FIG5

Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t ($di/dt < 100A/\mu s$)

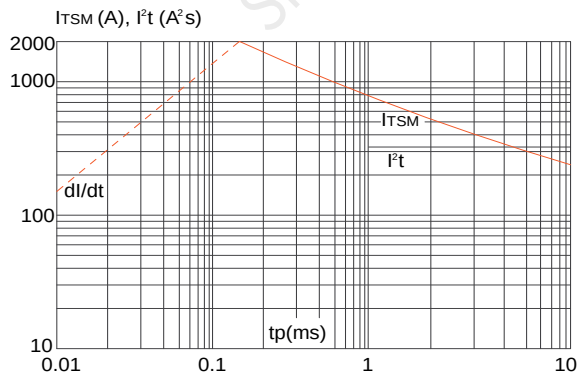
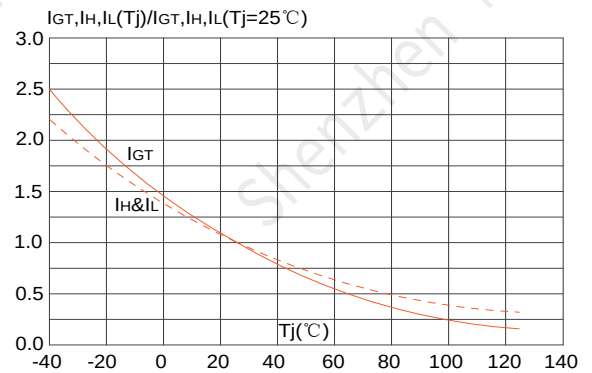
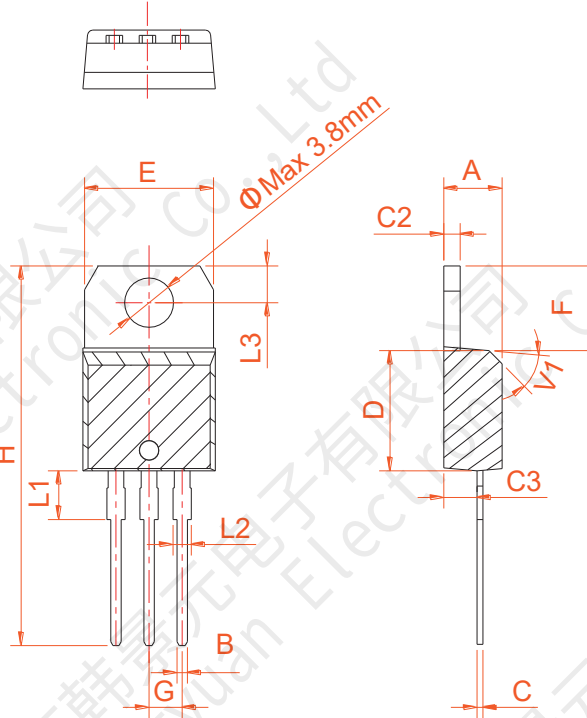


FIG6

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



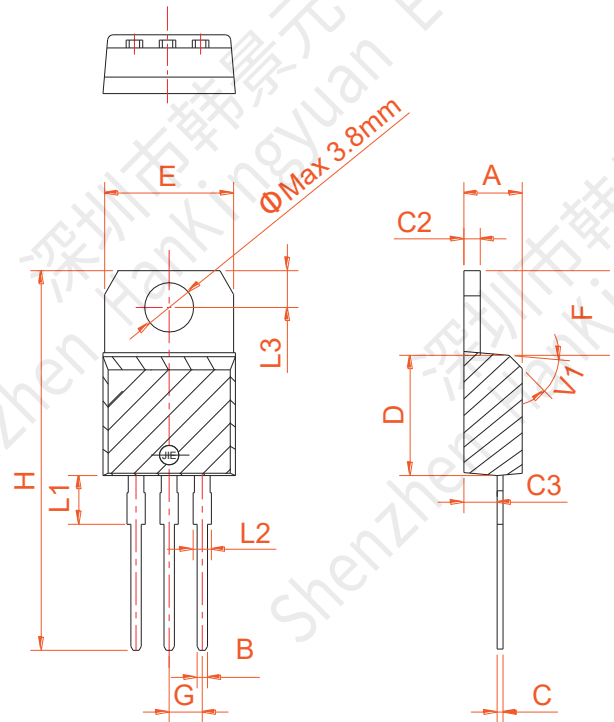
PACKAGE MECHANICAL DATA



TO-220A Ins

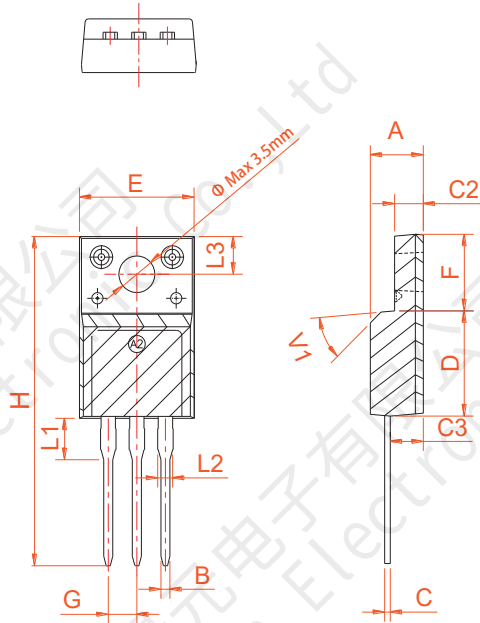
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



TO-220B Non-Ins

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	



ShenZhenHanKingyuan
Electronic CO.,Ltd

Information furnished is believed to be accurate and reliable. However, Shenzhen HanKingyuan Electronic assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied.

The KY logo is a registered trademark of Shenzhen HanKingyuan Electronic.

©2013 Shenzhen HanKingyuan Electronic – Printed in Shenzhen – All Rights Reserved